

## Inventor Name Search Result

Your Search was:

Last Name = BANG

First Name = WON

Application#	Patent#	Status	Date Filed	Title	Inventor Name 26
<u>60195900</u>	Not Issued	159	04/10/2000	CONCENTRATION PROFILE ON DEMAND GAS DELIVERY SYSTEM (INDIVIDUAL DIVERT LIQUID DELIVERY SYSTEM)	BANG, WON
<u>60106531</u>	Not Issued	159	10/31/1998	CORROSION RESISTANT COATING	BANG , WON
<u>10618187</u>	Not Issued	020	07/10/2003	IN SITU SUBSTRATE HOLDER LEVELING METHOD AND APPARATUS	BANG, WON
<u>10428967</u>	Not Issued	020	05/01/2003	LIFT PIN ASSEMBLY FOR SUBSTRATE PROCESSING	BANG, WON B.
<u>10374571</u>	Not Issued	030	02/24/2003	IN-SITU HEALTH CHECK OF LIQUID INJECTION VAPORIZER	BANG, WON B.
<u>10314401</u>	Not Issued	071	12/09/2002	AIR PUMPING TYPE FIXED QUANTITY DISPENSING CONTAINER	BANG, WON-SEO
<u>10222398</u>	Not Issued	030	08/15/2002	CLOG-RESISTANT GAS DELIVERY SYSTEM	BANG, WON
<u>10131001</u>	6629559	150	04/24/2002	MOLDS FOR CASTING WITH CUSTOMIZED INTERNAL STRUCTURE TO COLLAPSE UPON COOLING AND TO FACILITATE CONTROL OF HEAT TRANSFER	BANG, WON B.
<u>10081312</u>	Not Issued	030	02/21/2002	IMPROVED CORROSION RESISTANT COATING	BANG, WON
<u>09902283</u>	Not Issued	061	07/10/2001	CLOG RESISTANT INJECTION VALVE	BANG, WON
<u>09832168</u>	Not Issued	123	04/10/2001	CONCENTRATION PROFILE ON DEMAND GAS DELIVERY SYSTEM (INDIVIDUAL DIVERT DELIVERY SYSTEM)	BANG, WON
<u>09637839</u>	6346481	150	08/12/2000	METHOD OF REDUCING PITTING OF A COATED HEATER	BANG, WON
<u>09620630</u>	Not Issued	161	07/20/2000	DEPOSITION RESISTANT LINING FOR CVD CHAMBER	BANG, WON B.
<u>09577920</u>	6397922	150	05/24/2000	MOLDS FOR CASTING WITH CUSTOMIZED INTERNAL STRUCTURE TO COLLAPSE UPON COOLING AND TO FACILITATE	BANG, WON B.

				CONTROL OF HEAT TRANSFER	
<u>09565323</u>	Not Issued	161	05/05/2000	METHOD FOR MAKING PURCHASES USING AN INTERMEDIARY	BANG, WONG SHIH
<u>09428140</u>	6379492	150	10/26/1999	CORROSION RESISTANT COATING	BANG , WON
<u>09427777</u>	Not Issued	160	10/26/1999	CORROSION RESISTANT COATING	BANG , WON
<u>09248789</u>	6267820	150	02/12/1999	CLOG RESISTANT INJECTION VALVE	BANG , WON
<u>09163282</u>	6261374	150	09/29/1998	CLOG RESISTANT GAS DELIVERY SYSTEM	BANG , WON
<u>09144722</u>	5948958	150	09/01/1998	METHOD AND APPARATUS FOR VERIFYING THE CALIBRATION OF SEMICONDUCTOR PROCESSING EQUIPMENT	BANG , WON
<u>09105970</u>	6235120	150	06/26/1998	COATING FOR PARTS USED IN SEMICONDUCTOR PROCESSING CHAMBERS	BANG , WON
<u>09047284</u>	6117244	150	03/24/1998	DEPOSITION RESISTANT LINING FOR CVD CHAMBER	BANG, WON B.
<u>09009907</u>	6063198	150	01/21/1998	HIGH PRESSURE RELEASE DEVICE FOR SEMICONDUCTOR FABRICATING EQUIPMENT	BANG , WON
<u>08954299</u>	6090206	150	10/20/1997	THROTTLE VALVE PROVIDING ENHANCED CLEANING	BANG, WON B.
<u>08953444</u>	6110556	150	10/17/1997	LID ASSEMBLY FOR A PROCESS CHAMBER EMPLOYING ASYMMETRIC FLOW GEOMETRIES	BANG , WON
<u>08332780</u>	5591766	150	11/01/1994	SOLID ORAL FORMULATIONS OF PYRIDONE CARBOXYLIC ACIDS	BANG , WON Y.

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## Inventor Name Search Result

Your Search was:

Last Name = CHEN

First Name = CHEN-AN

Application#	Patent#	Status	Date Filed	Title	Inventor Name 44
<u>60513310</u>	Not Issued	020	10/21/2003	PLATING SYSTEM WITH INTEGRATED SUBSTRATE INSPECTION	CHEN, CHEN-AN
<u>60352191</u>	Not Issued	159	01/26/2002	APPARATUS AND METHOD OF GENERATION OF A PLASMA IN DEPOSITION PROCESSES	CHEN, CHEN-AN
<u>60287280</u>	Not Issued	159	04/28/2001	CHEMICAL VAPOR DEPOSITION CHAMBER	CHEN, CHEN-AN
<u>60106531</u>	Not Issued	159	10/31/1998	CORROSION RESISTANT COATING	CHEN , CHEN-AN
<u>10621042</u>	Not Issued	030	07/15/2003	METHOD AND APPARATUS FOR FLUID FLOW CONTROL	CHEN, CHEN-AN
<u>10453227</u>	Not Issued	030	06/02/2003	METHOD AND APPARATUS FOR PROCESSING SEMICONDUCTOR SUBSTRATES WITH HYDROXYL RADICALS	CHEN, CHEN-AN
<u>10373749</u>	Not Issued	041	02/27/2003	KEY RING WITH A DIAMOND-SHINING ORNAMENTAL BLOCK	CHENG, CHEN-AN
<u>10339390</u>	Not Issued	030	01/10/2003	ELASTIC FLASH STICK WITH AN ORNAMENTAL BLOCK	CHENG, CHEN-AN
<u>10302240</u>	Not Issued	041	11/22/2002	CVD PLASMA ASSISTED LOWER DIELECTRIC CONSTANT SICOH FILM	CHEN, CHEN-AN
<u>10219307</u>	<u>6513167</u>	150	08/16/2002	HEADBAND ASSEMBLY	CHENG, CHEN-AN
<u>10197940</u>	Not Issued	030	07/16/2002	APPARATUS AND METHOD FOR PLASMA ASSISTED DEPOSITION	CHEN, CHEN-AN
<u>10173408</u>	<u>6641262</u>	150	06/18/2002	EYEGLASSES WITH DIAMOND-SHINING EFFECT	CHENG, CHEN-AN
<u>10134206</u>	Not Issued	041	04/26/2002	CHEMICAL VAPOR DEPOSITION CHAMBER	CHEN, CHEN-AN
<u>10131402</u>	<u>6626184</u>	150	04/25/2002	OPEN-LOOP HEADBAND ASSEMBLY WITH A FLICKERING DECORATION LIGHT DEVICE	CHENG, CHEN-AN
<u>10122481</u>	Not Issued	030	04/12/2002	METHOD FOR CLEANING A PROCESS CHAMBER	CHEN, CHEN-AN
<u>10100148</u>	Not Issued	041	03/19/2002	ORNAMENTAL COMB ASSEMBLY	CHENG, CHEN-AN

<u>10081312</u>	Not Issued	030	02/21/2002	IMPROVED CORROSION RESISTANT COATING	CHEN, CHEN-AN
<u>09902283</u>	Not Issued	061	07/10/2001	CLOG RESISTANT INJECTION VALVE	CHEN, CHEN-AN
<u>09900900</u>	6546562	150	07/10/2001	ADJUSTABLE ENCIRCLING HEADBAND	CHENG, CHEN-AN
<u>09900898</u>	Not Issued	161	07/10/2001	CAP STRUCTURE OF A CONTAINER	CHENG, CHEN-AN
<u>09900857</u>	6382218	150	07/10/2001	OPEN-LOOP HEADBAND ASSEMBLY	CHENG, CHEN-AN
<u>09895104</u>	6591850	150	06/29/2001	METHOD AND APPARATUS FOR FLUID FLOW CONTROL	CHEN, CHEN-AN
<u>09885985</u>	6486082	150	06/18/2001	CVD PLASMA ASSISTED LOWER DIELECTRIC CONSTANT SICOH FILM	CHEN, CHEN-AN
<u>09882769</u>	6506994	150	06/15/2001	LOW PROFILE THICK FILM HEATERS IN MULTI-SLOT BAKE CHAMBER	CHEN, CHEN-AN
<u>09820586</u>	Not Issued	094	03/28/2001	PURGE HEATER DESIGN AND PROCESS DEVELOPMENT FOR THE IMPROVEMENT OF LOW K FILM PROPERTIES	CHEN, CHEN-AN
<u>09769475</u>	6398019	150	01/26/2001	CUP WITH INDICATING DEVICE FOR CELLULAR PHONE CALL	CHENG, CHEN-AN
<u>09696034</u>	6288498	150	10/26/2000	STRUCTURE OF FLICKERING DECORATION LIGHT	CHENG, CHEN-AN
<u>09637839</u>	6346481	150	08/12/2000	METHOD OF REDUCING PITTING OF A COATED HEATER	CHEN, CHEN-AN
<u>09561325</u>	6387207	150	04/28/2000	INTEGRATION OF REMOTE PLASMA GENERATOR WITH SEMICONDUCTOR PROCESSING CHAMBER	CHEN, CHEN-AN
<u>09557079</u>	6596343	150	04/21/2000	METHOD FOR PROCESSING SEMICONDUCTOR SUBSTRATES WITH HYDROXYL RADICALS	CHEN, CHEN-AN
<u>09550448</u>	6303501	150	04/17/2000	GAS MIXING APPARATUS AND METHOD	CHEN, CHEN-AN
<u>09428140</u>	6379492	150	10/26/1999	CORROSION RESISTANT COATING	CHEN , CHEN-AN
<u>09427777</u>	Not Issued	160	10/26/1999	CORROSION RESISTANT COATING	CHEN , CHEN-AN
<u>09342667</u>	6358327	150	06/29/1999	METHOD FOR ENDPOINT DETECTION USING THROTTLE VALVE POSITION	CHEN , CHEN-AN
<u>09290228</u>	6004055	250	04/13/1999	NAIL ENAMEL CONTAINER	CHENG , CHEN-AN
<u>09248789</u>	6267820	150	02/12/1999	CLOG RESISTANT INJECTION VALVE	CHEN , CHEN-AN
<u>09163282</u>	6261374	150	09/29/1998	CLOG RESISTANT GAS DELIVERY SYSTEM	CHEN , CHEN-AN



<u>09144722</u>	<u>5948958</u>	150	09/01/1998	METHOD AND APPARATUS FOR VERIFYING THE CALIBRATION OF SEMICONDUCTOR PROCESSING EQUIPMENT	CHEN , CHEN-AN
<u>09105970</u>	<u>6235120</u>	150	06/26/1998	COATING FOR PARTS USED IN SEMICONDUCTOR PROCESSING CHAMBERS	CHEN , CHEN-AN
<u>09004820</u>	<u>6110284</u>	150	01/09/1998	APPARATUS AND A METHOD FOR SHIELDING LIGHT EMANATING FROM A LIGHT SOURCE HEATING A SEMICONDUCTOR PROCESSING CHAMBER	CHEN , CHEN-AN
<u>08893414</u>	<u>6068703</u>	150	07/11/1997	GAS MIXING APPARATUS AND METHOD	CHEN , CHEN-AN
<u>08890805</u>	<u>6024799</u>	150	07/11/1997	CHEMICAL VAPOR DEPOSITION MANIFOLD	CHEN , CHEN-AN
<u>08755219</u>	Not Issued	168	11/22/1996	HIGH TEMPERATURE RESISTIVE HEATER	CHEN , CHEN-AN
<u>08717780</u>	<u>6066836</u>	150	09/23/1996	HIGH TEMPERATURE RESISTIVE HEATER FOR A PROCESS CHAMBER	CHEN , CHEN-AN

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## Inventor Name Search Result

Your Search was:

Last Name = VENKATARAMAN

First Name = SHANKAR

Application#	Patent#	Status	Date Filed	Title	Inventor Name 35
<u>60143091</u>	Not Issued	159	07/09/1999	APPARATUS FOR DISTRIBUTING GASES IN A CHEMICAL VAPOR DEPOSITION SYSTEM	VENKATARAMAN , SHANKAR
<u>10621042</u>	Not Issued	030	07/15/2003	METHOD AND APPARATUS FOR FLUID FLOW CONTROL	VENKATARAMAN, SHANKAR
<u>10449260</u>	Not Issued	020	05/30/2003	METHOD AND SYSTEM FOR TRANSPORTING FAULTS ACROSS A NETWORK	VENKATARAMAN, SHANKAR
<u>10383837</u>	Not Issued	071	03/07/2003	METHOD OF IMPROVING INTERLAYER ADHESION	VENKATARAMAN, SHANKAR
<u>10375853</u>	Not Issued	041	02/25/2003	METHOD OF DEPOSITING LOW DIELECTRIC CONSTANT SILICON CARBIDE LAYERS	VENKATARAMAN, SHANKAR
<u>10375793</u>	Not Issued	030	02/25/2003	METHOD OF DEPOSITING LOW DIELECTRIC CONSTANT SILICON CARBIDE LAYERS	VENKATARAMAN, SHANKAR
<u>10365061</u>	Not Issued	030	02/12/2003	EFFICIENT FRAMING PROCEDURE FOR VARIABLE LENGTH PACKETS	VENKATARAMAN, SHANKAR
<u>10354214</u>	Not Issued	030	01/27/2003	METHOD AND APPARATUS FOR CLEANING A CVD CHAMBER	VENKATARAMAN, SHANKAR
<u>10346836</u>	Not Issued	030	01/16/2003	CLEANING OF CVD CHAMBERS USING REMOTE SOURCE WITH CXFYOZ BASED CHEMISTRY	VENKATARAMAN, SHANKAR
<u>10327209</u>	Not Issued	030	12/20/2002	BLOCKER PLATE BYPASS DESIGN TO IMPROVE CLEAN RATE AT THE EDGE OF THE CHAMBER	VENKATARAMAN, SHANKAR
<u>10302350</u>	Not Issued	030	11/22/2002	METHOD FOR CLEANING PLASMA ENHANCED CHEMICAL VAPOR DEPOSITION CHAMBER USING VERY HIGH FREQUENCY ENERGY	VENKATARAMAN, SHANKAR
<u>10302240</u>	Not Issued	041	11/22/2002	CVD PLASMA ASSISTED LOWER DIELECTRIC CONSTANT SICOH FILM	VENKATARAMAN, SHANKAR
<u>10279367</u>	Not Issued	093	10/23/2002	PLASMA ENHANCED CVD LOW K CARBON-DOPED SILICON OXIDE FILM DEPOSITION USING VHF-RF POWER	VENKATARAMAN, SHANKAR



<u>10245443</u>	Not Issued	041	09/16/2002	HEATED GAS DISTRIBUTION PLATE FOR A PROCESSING CHAMBER	VENKATARAMAN, SHANKAR
<u>10245442</u>	Not Issued	030	09/16/2002	METHODS FOR OPERATING A CHEMICAL VAPOR DEPOSITION CHAMBER USING A HEATED GAS DISTRIBUTION PLATE	VENKATARAMAN, SHANKAR
<u>10196498</u>	Not Issued	030	07/15/2002	METHOD OF DEPOSITING DIELECTRIC MATERIALS IN DAMASCENE APPLICATIONS	VENKATARAMAN, SHANKAR
<u>10183566</u>	Not Issued	030	06/28/2002	NEEDLE CONTROLLED FUEL INJECTOR WITH TWO CONTROL VALVES	VENKATARAMAN, SHANKAR C.
<u>10122481</u>	Not Issued	030	04/12/2002	METHOD FOR CLEANING A PROCESS CHAMBER	VENKATARAMAN, SHANKAR
<u>10115665</u>	Not Issued	030	04/03/2002	ACCELERATED PLASMA CLEAN	VENKATARAMAN, SHANKAR
<u>10081312</u>	Not Issued	030	02/21/2002	IMPROVED CORROSION RESISTANT COATING	VENKATARAMAN, SHANKAR
<u>09942328</u>	Not Issued	041	08/28/2001	STREAMLINED CACHE COHERENCY PROTOCOL SYSTEM AND METHOD FOR A MULTIPLE PROCESSOR SINGLE CHIP DEVICE	VENKATARAMAN, SHANKAR
<u>09916598</u>	Not Issued	041	07/26/2001	CACHE COHERENT SPLIT TRANSACTION MEMORY BUS ARCHITECTURE AND PROTOCOL FOR A MULTI PROCESSOR CHIP DEVICE	VENKATARAMAN, SHANKAR
<u>09895104</u>	<u>6591850</u>	150	06/29/2001	METHOD AND APPARATUS FOR FLUID FLOW CONTROL	VENKATARAMAN, SHANKAR
<u>09885985</u>	<u>6486082</u>	150	06/18/2001	CVD PLASMA ASSISTED LOWER DIELECTRIC CONSTANT SICOH FILM	VENKATARAMAN, SHANKAR
<u>09865605</u>	Not Issued	030	05/29/2001	CHIP MULTIPROCESSOR WITH MULTIPLE OPERATING SYSTEMS	VENKATARAMAN, SHANKAR
<u>09820586</u>	Not Issued	094	03/28/2001	PURGE HEATER DESIGN AND PROCESS DEVELOPMENT FOR THE IMPROVEMENT OF LOW K FILM PROPERTIES	VENKATARAMAN, SHANKAR
<u>09793818</u>	<u>6537733</u>	150	02/23/2001	METHOD OF DEPOSITING LOW DIELECTRIC CONSTANT SILICON CARBIDE LAYERS	VENKATARAMAN, SHANKAR
<u>09657392</u>	Not Issued	071	09/08/2000	DUAL PLASMA TREATMENT OF SILICON CARBIDE FILMS	VENKATARAMAN, SHANKAR
<u>09633078</u>	Not Issued	161	08/04/2000	METHOD AND APPARATUS FOR REMOVING SILICON CARBIDE FROM SEMICONDUCTOR SUBSTRATES	VENKATARAMAN, SHANKAR
<u>09609994</u>	<u>6495233</u>	150	07/05/2000	APPARATUS FOR DISTRIBUTING	VENKATARAMAN,

				GASES IN A CHEMICAL VAPOR DEPOSITION SYSTEM	SHANKAR
<u>09561325</u>	<u>6387207</u>	150	04/28/2000	INTEGRATION OF REMOTE PLASMA GENERATOR WITH SEMICONDUCTOR PROCESSING CHAMBER	VENKATARAMAN, SHANKAR
<u>09428140</u>	<u>6379492</u>	150	10/26/1999	CORROSION RESISTANT COATING	VENKATARAMAN, SHANKAR
<u>09338470</u>	<u>6413583</u>	150	06/22/1999	FORMATION OF A LIQUID-LIKE SILICA LAYER BY REACTION OF AN ORGANOSILICON COMPOUND AND A HYDROXYL FORMING COMPOUND	VENKATARAMAN, SHANKAR
<u>09246036</u>	<u>6374831</u>	150	02/04/1999	ACCELERATED PLASMA CLEAN	VENKATARAMAN, SHANKAR
<u>08865505</u>	Not Issued	161	05/30/1997	METHOD AND SYSTEM FOR RECORDING AND REPRODUCING INFORMATION	VENKATARAMAN, SHANKAR

Inventor Search Completed: No Records to Display.

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## Inventor Name Search Result

Your Search was:

Last Name = BHATNAGAR

First Name = AJAY

Application#	Patent#	Status	Date Filed	Title	Inventor Name 8
<a href="#">60425482</a>	Not Issued	020	11/12/2002	ORGANIC COMPOUNDS	BHATNAGAR, AJAY S.
<a href="#">60294094</a>	Not Issued	159	05/29/2001	METHOD AND SYSTEM FOR LOGGING INTO AND PROVIDING ACCESS TO A COMPUTER SYSTEM VIA A COMMUNICATIONS NETWORK	BHATNAGAR, AJAY
<a href="#">10081312</a>	Not Issued	030	02/21/2002	IMPROVED CORROSION RESISTANT COATING	BHATNAGAR, AJAY
<a href="#">09428140</a>	<a href="#">6379492</a>	150	10/26/1999	CORROSION RESISTANT COATING	BHATNAGAR , AJAY
<a href="#">08300668</a>	<a href="#">5583128</a>	150	09/02/1994	CONTRACEPTION IN FEMALE PRIMATES WITHOUT AFFECTING THE MENSTRUAL CYCLE	BHATNAGAR , AJAY
<a href="#">08195892</a>	Not Issued	164	02/10/1994	CONTRACEPTION IN FEMALE PRIMATES WITHOUT AFFECTING THE MENSTRUAL CYCLE	BHATNAGAR , AJAY
<a href="#">07872272</a>	Not Issued	166	04/22/1992	CONTRACEPTION IN FEMALE PRIMATES WITHOUT AFFECTING THE MENSTRUAL CYCLE	BHATNAGAR , AJAY
<a href="#">07412369</a>	<a href="#">5057521</a>	150	09/26/1989	USE OF BICYCLIC IMIDAZOLE COMPOUNDS FOR THE TREATMENT OF HYPERALDOSTERONISM	BHATNAGAR , AJAY

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L Number	Hits	Search Text	DB	Time stamp
1	2	6346481.pn. or 6235120.pn.	USPAT; US-PGPUB	2004/01/29 09:32
2	3	(Bang.in. or Chen.in. or Venkataraman.in. or Bhatnagar.in. or (Applied adj Material).as.) and ((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3)) same (density) same (purity)	USPAT; US-PGPUB	2004/01/29 10:01
3	3	(Bang.in. or Chen.in. or Venkataraman.in. or Bhatnagar.in. or (Applied adj Material).as.) and ((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride))) same (density) same (purity)	USPAT; US-PGPUB	2004/01/29 09:46
4	0	((Bang.in. or Chen.in. or Venkataraman.in. or Bhatnagar.in. or (Applied adj Material).as.) and ((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride))) same (density) same (purity)) not ((Bang.in. or Chen.in. or Venkataraman.in. or Bhatnagar.in. or (Applied adj Material).as.) and ((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3)) same (density) same (purity))	USPAT; US-PGPUB	2004/01/29 09:37
5	17	(Bang.in. or Chen.in. or Venkataraman.in. or Bhatnagar.in. or (Applied adj Material).as.) and ((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3)) same ((corros\$3 or corroded\$3 or protect\$3 or pit or pitted or pitting or defect\$3 or damage\$3) with (fluorine or NF3 or "NF.sub.3" or CHF3 or "CHF.sub.3" or heater or aluminum or Al or AlN or (aluminum adj nitride) or support or pedestal or susceptor))	USPAT; US-PGPUB	2004/01/29 10:50
6	14	((Bang.in. or Chen.in. or Venkataraman.in. or Bhatnagar.in. or (Applied adj Material).as.) and ((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3)) same ((corros\$3 or corroded\$3 or protect\$3 or pit or pitted or pitting or defect\$3 or damage\$3) with (fluorine or NF3 or "NF.sub.3" or CHF3 or "CHF.sub.3" or heater or aluminum or Al or AlN or (aluminum adj nitride) or support or pedestal or susceptor))) not ((Bang.in. or Chen.in. or Venkataraman.in. or Bhatnagar.in. or (Applied adj Material).as.) and ((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride))) same (density) same (purity))	USPAT; US-PGPUB	2004/01/29 09:41
7	1	(Bang or Chen or Venkataraman or Bhatnagar or (Applied adj Material)) and ((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride))) same (density) same (purity)	EPO; JPO; DERWENT; IBM_TDB	2004/01/29 09:47



8	5	(Bang or Chen or Venkataraman or Bhatnagar or (Applied adj Material)) and ((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3)) and ((corros\$3 or corroded\$3 or protect\$3 or pit or pitted or pitting or defect\$3 or damag\$3) with (fluorine or NF3 or "NF.sub.3" or CHF3 or "CHF.sub.3" or heater or aluminum or Al or AlN or (aluminum adj nitride) or support or pedestal or susceptor))	EPO; JPO; DERWENT; IBM_TDB	2004/01/29 09:48
9	5	((Bang or Chen or Venkataraman or Bhatnagar or (Applied adj Material)) and ((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3)) and ((corros\$3 or corroded\$3 or protect\$3 or pit or pitted or pitting or defect\$3 or damag\$3) with (fluorine or NF3 or "NF.sub.3" or CHF3 or "CHF.sub.3" or heater or aluminum or Al or AlN or (aluminum adj nitride) or support or pedestal or susceptor))) not ((Bang or Chen or Venkataraman or Bhatnagar or (Applied adj Material)) and ((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride))) same (density) same (purity))	EPO; JPO; DERWENT; IBM_TDB	2004/01/29 09:59
10	1924	(427/585,593,596,255.28,255.39).CCLS.	USPAT; US-PGPUB	2004/01/29 09:59
11	1918	(427/372.2,383.1).CCLS.	USPAT; US-PGPUB	2004/01/29 10:00
12	548	(423/490,497).CCLS.	USPAT; US-PGPUB	2004/01/29 10:00
13	4257	(118/715,725,728).CCLS.	USPAT; US-PGPUB	2004/01/29 10:00
14	8487	((427/585,593,596,255.28,255.39).CCLS.) ((427/372.2,383.1).CCLS.) ((423/490,497).CCLS.) ((118/715,725,728).CCLS.)	USPAT; US-PGPUB	2004/01/29 10:00
15	0	((423/490,497).CCLS.) and (((427/585,593,596,255.28,255.39).CCLS.) or ((427/372.2,383.1).CCLS.) or ((118/715,725,728).CCLS.))	USPAT; US-PGPUB	2004/01/29 10:00
16	3	((427/585,593,596,255.28,255.39).CCLS.) ((427/372.2,383.1).CCLS.) ((423/490,497).CCLS.) ((118/715,725,728).CCLS.)) and ((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3)) same (density or dense) same (purity or pure or impure or impurit\$3)	USPAT; US-PGPUB	2004/01/29 13:08
17	1	6162495.pn.	USPAT; US-PGPUB	2004/01/29 10:03
18	31	((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3)) same (density or dense) same (purity or pure or impure or impurit\$3)	USPAT; US-PGPUB	2004/01/29 10:08

19	28	((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3)) same (density or dense) same (purity or pure or impure or impurit\$3)) not (((427/585,593,596,255.28,255.39).CCLS.) (427/372.2,383.1).CCLS.) (423/490,497).CCLS.) (118/715,725,728).CCLS.)) and ((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3)) same (density or dense) same (purity or pure or impure or impurit\$3))	USPAT; US-PGPUB	2004/01/29 10:04
20	23	((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3)) with (density or dense)) and (((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3)) with (purity or pure or impure or impurit\$3))	USPAT; US-PGPUB	2004/01/29 12:44
21	9	((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3)) with (density or dense)) and ((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3)) with (purity or pure or impure or impurit\$3)) not ((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3)) same (density or dense) same (purity or pure or impure or impurit\$3))	USPAT; US-PGPUB	2004/01/29 10:09
22	38	((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) ) with (density or dense)) and ((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) ) with (purity or pure or impure or impurit\$3))	USPAT; US-PGPUB	2004/01/29 10:13



23	15	(((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) ) with (density or dense)) and (((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) ) with (purity or pure or impure or impurit\$3))) not (((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3)) same (density or dense) same (purity or pure or impure or impurit\$3)) or (((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3)) with (density or dense)) and (((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3)) with (purity or pure or impure or impurit\$3))))	USPAT; US-PGPUB	2004/01/29 10:13
24	48	(((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3)) same (density or dense)) and (((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3)) same (purity or pure or impure or impurit\$3))))	USPAT; US-PGPUB	2004/01/29 10:31

25	8	(((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3)) same (density or dense)) and (((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3)) same (purity or pure or impure or impurit\$3))) not (((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3)) same (density or dense) same (purity or pure or impure or impurit\$3)) not (((427/585,593,596,255.28,255.39).CCLS.) ((427/372.2,383.1).CCLS.) ((423/490,497).CCLS.) ((118/715,725,728).CCLS.)) and ((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3)) same (density or dense) same (purity or pure or impure or impurit\$3))) or (((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3)) with (density or dense)) and (((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3)) with (purity or pure or impure or impurit\$3))) or (((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) ) with (density or dense)) and (((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) ) with (purity or pure or impure or impurit\$3))))	USPAT; US-PGPUB	2004/01/29 10:28
26	53	(((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3 or EB or (electron adj beam))) same (density or dense) same (temperature))	USPAT; US-PGPUB	2004/01/29 11:28
27	77	(((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) same (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3 or EB or (electron adj beam))) same (density or dense) same (temperature or temp\$8))	USPAT; US-PGPUB	2004/01/29 12:10



28	24	((((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) same (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3 or EB or (electron adj beam))) same (density or dense) same (temperature or temp\$8)) ) not (((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3 or EB or (electron adj beam))) same (density or dense) same (temperature)) )	USPAT; US-PGPUB	2004/01/29 10:39
29	386	((((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3 or EB or (electron adj beam)))) and ((density or dense) with (temperature or temp\$8)))	USPAT; US-PGPUB	2004/01/29 11:29
30	161	((((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3 or EB or (electron adj beam)))) and ((density or dense) with (temperature or temp\$8) with (coat\$3 or film or layer or deposit\$3 or apply\$3 or \$4CVD or EB or (electron adj beam))) ) )	USPAT; US-PGPUB	2004/01/29 10:42
31	11	((427/585,593,596,255.28,255.39).CCLS.) ((427/372.2,383.1).CCLS.) ((423/490,497).CCLS.) ((118/715,725,728).CCLS.)) and ((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3)) same ((corros\$3 or corroded\$3 or protect\$3 or pit or pitted or pitting or defect\$3 or damag\$3) with (fluorine or NF3 or "NF.sub.3" or CHF3 or "CHF.sub.3" or heater or aluminum or Al or AlN or (aluminum adj nitride) or support or pedestal or susceptor))	USPAT; US-PGPUB	2004/01/29 10:54
32	306	((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3)) same ((corros\$3 or corroded\$3 or protect\$3 or pit or pitted or pitting or defect\$3 or damag\$3) with (fluorine or NF3 or "NF.sub.3" or CHF3 or "CHF.sub.3" or heater or aluminum or Al or AlN or (aluminum adj nitride) or support or pedestal or susceptor))	USPAT; US-PGPUB	2004/01/29 11:30

33	295	((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3)) same ((corros\$3 or corroded\$3 or protect\$3 or pit or pitted or pitting or defect\$3 or damag\$3) with (fluorine or NF3 or "NF.sub.3" or CHF3 or "CHF.sub.3" or heater or aluminum or Al or AlN or (aluminum adj nitride) or support or pedestal or susceptor))) not (((427/585,593,596,255.28,255.39).CCLS.) ((427/372.2,383.1).CCLS.) ((423/490,497).CCLS.) ((118/715,725,728).CCLS.)) and ((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3)) same ((corros\$3 or corroded\$3 or protect\$3 or pit or pitted or pitting or defect\$3 or damag\$3) with (fluorine or NF3 or "NF.sub.3" or CHF3 or "CHF.sub.3" or heater or aluminum or Al or AlN or (aluminum adj nitride) or support or pedestal or susceptor)))	USPAT; US-PGPUB	2004/01/29 10:55
34	643	((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3)) with ((corros\$3 or corroded\$3 or protect\$3 or pit or pitted or pitting or defect\$3 or damag\$3))	USPAT; US-PGPUB	2004/01/29 11:33
35	49	((427/585,593,596,255.28,255.39).CCLS.) ((427/372.2,383.1).CCLS.) ((423/490,497).CCLS.) ((118/715,725,728).CCLS.)) and ((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3)) with ((corros\$3 or corroded\$3 or protect\$3 or pit or pitted or pitting or defect\$3 or damag\$4 or fluorine or NF3 or "NF.sub.3" or CHF3 or "CHF.sub.3" or heater or aluminum or Al or AlN or (aluminum adj nitride) or support or pedestal or susceptor))	USPAT; US-PGPUB	2004/01/29 11:08
36	0	((427/585,593,596,255.28,255.39).CCLS.) ((427/372.2,383.1).CCLS.) ((423/490,497).CCLS.) ((118/715,725,728).CCLS.)) and ((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3)) and (density or dense) and (purity or pure or impure or impurit\$3)	EPO; JPO; DERWENT; IBM_TDB	2004/01/29 11:25
37	5	((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3)) and (density or dense) and (purity or pure or impure or impurit\$3)	EPO; JPO; DERWENT; IBM_TDB	2004/01/29 11:26
38	31	((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) ) and (density or dense) and (purity or pure or impure or impurit\$3)	EPO; JPO; DERWENT; IBM_TDB	2004/01/29 11:26



39	26	((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) ) and (density or dense) and (purity or pure or impure or impurit\$3)) not ((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3)) and (density or dense) and (purity or pure or impure or impurit\$3))	EPO; JPO; DERWENT; IBM_TDB	2004/01/29 11:26
40	7	((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3 or EB or (electron adj beam))) same (density or dense) same (temperature))	EPO; JPO; DERWENT; IBM_TDB	2004/01/29 11:28
41	8	((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3 or EB or (electron adj beam))) and ((density or dense) with (temperature or temp\$8))	EPO; JPO; DERWENT; IBM_TDB	2004/01/29 11:29
42	4	((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3 or EB or (electron adj beam))) and ((density or dense) with (temperature or temp\$8)) ) not ((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3 or EB or (electron adj beam))) same (density or dense) same (temperature)) )	EPO; JPO; DERWENT; IBM_TDB	2004/01/29 11:29
43	78	((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3)) same ((corros\$3 or corroded\$3 or protect\$3 or pit or pitted or pitting or defect\$3 or damag\$3) with (fluorine or NF3 or "NF.sub.3" or CHF3 or "CHF.sub.3" or heater or aluminum or Al or AlN or (aluminum adj nitride) or support or pedestal or susceptor))	EPO; JPO; DERWENT; IBM_TDB	2004/01/29 11:30
44	245	((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3)) with ((corros\$3 or corroded\$3 or protect\$3 or pit or pitted or pitting or defect\$3 or damag\$3))	EPO; JPO; DERWENT; IBM_TDB	2004/01/29 11:54

45	177	((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3)) with ((corros\$3 or corrod\$3 or protect\$3 or pit or pitted or pitting or defect\$3 or damag\$3))) not (((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3)) same ((corros\$3 or corrod\$3 or protect\$3 or pit or pitted or pitting or defect\$3 or damag\$3) with (fluorine or NF3 or "NF.sub.3" or CHF3 or "CHF.sub.3" or heater or aluminum or Al or AlN or (aluminum adj nitride) or support or pedestal or susceptor)))	EPO; JPO; DERWENT; IBM_TDB	2004/01/29 11:34
46	1003	((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3 or EB or EBPVD or (electron adj beam))) same ((corros\$3 or corrod\$3 or protect\$3 or pit or pitted or pitting or defect\$3 or damag\$3))	USPAT; US-PGPUB	2004/01/29 12:00
47	196	((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3 or EB or EBPVD or (electron adj beam))) same ((corros\$3 or corrod\$3 or protect\$3 or pit or pitted or pitting or defect\$3 or damag\$3))) and ((coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3 or EB or EBPVD or (electron adj beam)) same temperature same pressure)	USPAT; US-PGPUB	2004/01/29 11:57
48	67	((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3 or EB or EBPVD or (electron adj beam))) same ((corros\$3 or corrod\$3 or protect\$3 or pit or pitted or pitting or defect\$3 or damag\$3))) and ((coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3 or EB or EBPVD or (electron adj beam)) with temperature with pressure)	USPAT; US-PGPUB	2004/01/29 11:57
49	98	((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3 or EB or EBPVD or (electron adj beam))) same temperature same pressure	USPAT; US-PGPUB	2004/01/29 12:06
50	15	((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3 or EB or EBPVD or (electron adj beam))) same temperature same pressure	EPO; JPO; DERWENT; IBM_TDB	2004/01/29 12:06
51	32	((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3 or EB or (electron adj beam))) same (porous or porosity or nonporous or packed or packing or pack) same (temperature or temp\$8))	USPAT; US-PGPUB	2004/01/29 12:18



52	4	((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride)) same (EB or (electron adj beam) or EBCVD or EBPVD)) same (porous or porosity or nonporous or packed or packing or pack or dens\$4) same (temperature or temp\$8))	USPAT; US-PGPUB	2004/01/29 12:19
53	8	((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride)) same (EB or (electron adj beam) or EBCVD or EBPVD)) same (porous or porosity or nonporous or packed or packing or pack or dens\$4) same (pur\$4 or impur\$6 or contamin\$5))	USPAT; US-PGPUB	2004/01/29 12:20
54	13	((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride)) same (EB or (electron adj beam) or EBCVD or EBPVD)) same temperature same pressure)	USPAT; US-PGPUB	2004/01/29 12:27
55	27	((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride)) same (EB or (electron adj beam) or EBCVD or EBPVD)) and (high\$3 adj temperature) and ((low\$3 or reduc\$5 or vacuum) near2 pressure))	USPAT; US-PGPUB	2004/01/29 12:25
56	54	((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride)) same (EB or (electron adj beam) or EBCVD or EBPVD)) and ((substrate or deposit\$3 or EB or (electron adj beam) or EBCVD or EBPVD or coat\$3) near8 temperature) and ((chamber or reactor or vessel or deposit\$3 or EB or (electron adj beam) or EBCVD or EBPVD or coat\$3) near8 pressure))	USPAT; US-PGPUB	2004/01/29 12:59
57	42	((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride)) same (EB or (electron adj beam) or EBCVD or EBPVD)) and ((substrate or deposit\$3 or EB or (electron adj beam) or EBCVD or EBPVD or coat\$3) near8 temperature) and ((chamber or reactor or vessel or deposit\$3 or EB or (electron adj beam) or EBCVD or EBPVD or coat\$3) near8 pressure)) not (((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride)) same (EB or (electron adj beam) or EBCVD or EBPVD)) same temperature same pressure) )	USPAT; US-PGPUB	2004/01/29 12:27
58	25	((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3)) with (density or dense or pack\$3 or void or pore or porous or nonporous)) and ((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3)) with (purity or pure or impure or impurit\$3 or contamin\$6))	USPAT; US-PGPUB	2004/01/29 12:45

59	2	(((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3)) with (density or dense or pack\$3 or void or pore or porous or nonporous)) and (((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3)) with (purity or pure or impure or impurit\$3 or contamin\$6))) not (((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3)) same (density or dense) same (purity or pure or impure or impurit\$3)) or (((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3)) with (density or dense)) and (((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3)) with (purity or pure or impure or impurit\$3))))	USPAT; US-PGPUB	2004/01/29 12:45
60	10	(((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride)) with temperature with "300"))	USPAT; US-PGPUB	2004/01/29 13:00
61	87	(((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride)) with "300"))	USPAT; US-PGPUB	2004/01/29 13:00
62	716	((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3)) and ((heater or susceptor or substrate or pedestal) with (polish\$4 or rough\$5 or smooth\$3 or 10RA or RA10))	USPAT; US-PGPUB	2004/01/29 13:11
63	36	((MgF2 or "MgF.sub.2" or (magnesium near2 fluoride) or (magnesium near2 halide) or (metal near2 fluoride)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3)) and ((heater or susceptor or substrate or pedestal) with (polish\$4 or rough\$5 or smooth\$3 or 10RA or RA10) with (before or prior or previous\$2 or pretreat\$4 or (pre adj treat\$4)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3))	USPAT; US-PGPUB	2004/01/29 13:13
64	40	((heater or susceptor or pedestal) with (polish\$4 or rough\$5 or smooth\$3 or 10RA or RA10) with (before or prior or previous\$2 or pretreat\$4 or (pre adj treat\$4)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3))	USPAT; US-PGPUB	2004/01/29 13:20
65	586	((heater or susceptor or pedestal) with (polish\$4 or rough\$5 or smooth\$3 or 10RA or RA10) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3))	USPAT; US-PGPUB	2004/01/29 13:27
66	33	((heater or susceptor or pedestal) with (polish\$4 or rough\$5 or smooth\$3 or 10RA or RA10) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3))) and ((427/585,593,596,255.28,255.39).CCLS.) ((427/372.2,383.1).CCLS.) ((423/490,497).CCLS.) ((118/715,725,728).CCLS.))	USPAT; US-PGPUB	2004/01/29 13:16

67	4	((heater or susceptor or pedestal) with (polish\$4 or smooth\$3) with (rough\$5 or 10RA or RA10) with (before or prior or previous\$2 or pretreat\$4 or (pre adj treat\$4)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3))	USPAT; US-PGPUB	2004/01/29 13:21
68	616	((polish\$4 or smooth\$3) with (rough\$5 or 10RA or RA10) with (before or prior or previous\$2 or pretreat\$4 or (pre adj treat\$4)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3))	USPAT; US-PGPUB	2004/01/29 13:27
69	21	((polish\$4 or smooth\$3) with (rough\$5 or 10RA or RA10) with (before or prior or previous\$2 or pretreat\$4 or (pre adj treat\$4)) with (coat\$3 or film or layer or deposit\$3 or \$4CVD or apply\$3))) and (((427/585,593,596,255.28,255.39).CCLS.) ((427/372.2,383.1).CCLS.) ((423/490,497).CCLS.) ((118/715,725,728).CCLS.))	USPAT; US-PGPUB	2004/01/29 13:21
70	12	((polish\$4 or smooth\$3) with (rough\$5 or 10RA or RA10) with (before or prior or previous\$2 or pretreat\$4 or (pre adj treat\$4)) with (\$4CVD or \$4PVD or EB or (electron adj beam)))	USPAT; US-PGPUB	2004/01/29 13:24
71	16	((polish\$4 or smooth\$3) with (rough\$5 or 10RA or RA10) with (before or prior or previous\$2 or pretreat\$4 or (pre adj treat\$4)) with (\$4CVD or \$4PVD or EB or (electron adj beam) or (vapor near2 deposit\$3)))	USPAT; US-PGPUB	2004/01/29 13:25
72	279	((polish\$4 or smooth\$3) with (before or prior or previous\$2 or pretreat\$4 or (pre adj treat\$4)) with (\$4CVD or \$4PVD or EB or (electron adj beam) or (vapor near2 deposit\$3)))	USPAT; US-PGPUB	2004/01/29 13:25
73	11	((polish\$4 or smooth\$3) with (before or prior or previous\$2 or pretreat\$4 or (pre adj treat\$4)) with (\$4CVD or \$4PVD or EB or (electron adj beam) or (vapor near2 deposit\$3)) with (benefi\$7 or advantag\$7 or optima\$7 or prefer\$6))	USPAT; US-PGPUB	2004/01/29 13:26
74	607	((heater or susceptor or pedestal or chuck or support) with (polish\$4 or smooth\$3) with (rough\$5 or 10RA or RA10))	USPAT; US-PGPUB	2004/01/29 13:31
75	15	((heater or susceptor or pedestal or chuck or support) with (polish\$4 or smooth\$3) with (rough\$5 or 10RA or RA10))) and (((427/585,593,596,255.28,255.39).CCLS.) ((427/372.2,383.1).CCLS.) ((423/490,497).CCLS.) ((118/715,725,728).CCLS.))	USPAT; US-PGPUB	2004/01/29 13:29
76	926	((heater or susceptor or pedestal or chuck or support) with (polish\$4 or smooth\$3) with (prefer\$6 or advantageous\$6 or benefi\$8 or desir\$6 or optim\$6))	USPAT; US-PGPUB	2004/01/29 13:36
77	8	((heater or susceptor or pedestal or chuck or support) with (polish\$4 or smooth\$3) with (prefer\$6 or advantageous\$6 or benefi\$8 or desir\$6 or optim\$6))) and (((427/585,593,596,255.28,255.39).CCLS.) ((427/372.2,383.1).CCLS.) ((423/490,497).CCLS.) ((118/715,725,728).CCLS.))	USPAT; US-PGPUB	2004/01/29 13:34
78	3	((heater or susceptor or pedestal or chuck or support) with (polish\$4 or smooth\$3) with (prefer\$6 or advantageous\$6 or benefi\$8 or desir\$6 or optim\$6) with (heat near2 transfer\$6))	USPAT; US-PGPUB	2004/01/29 13:38



80	1	((heater or susceptor or pedestal or chuck or support) with (polish\$4 or smooth\$3) with (heat near2 transfer\$6))) and (((427/585,593,596,255.28,255.39).CCLS.) ((427/372.2,383.1).CCLS.) ((423/490,497).CCLS.) ((118/715,725,728).CCLS.))	USPAT; US-PGPUB	2004/01/29 13:38
79	92	((heater or susceptor or pedestal or chuck or support) with (polish\$4 or smooth\$3) with (heat near2 transfer\$6))	USPAT; US-PGPUB	2004/01/29 13:57
81	9	((MgF2 or "MgF.sub.2" or (magnesium adj fluoride)) with (coat\$3 or film or layer) with (anneal\$5 or heat\$3) with (poros\$3 or void or dens\$9 or porous or nonporous or pack\$3))	USPAT; US-PGPUB	2004/01/29 14:00
82	158	((MgF2 or "MgF.sub.2" or (magnesium adj fluoride)) with (coat\$3 or film or layer) with (anneal\$5 or heat\$3))	USPAT; US-PGPUB	2004/01/29 14:07
83	149	((MgF2 or "MgF.sub.2" or (magnesium adj fluoride)) with (coat\$3 or film or layer) with (anneal\$5 or heat\$3))) not (((MgF2 or "MgF.sub.2" or (magnesium adj fluoride)) with (coat\$3 or film or layer) with (anneal\$5 or heat\$3) with (poros\$3 or void or dens\$9 or porous or nonporous or pack\$3)))	USPAT; US-PGPUB	2004/01/29 14:00
84	20	((MgF2 or "MgF.sub.2" or (magnesium adj fluoride)) with anneal\$4)	USPAT; US-PGPUB	2004/01/29 14:13
85	18	((MgF2 or "MgF.sub.2" or (magnesium adj fluoride)) with (heat\$3 near2 treat\$6))	USPAT; US-PGPUB	2004/01/29 14:10
86	4	((MgF2 or "MgF.sub.2" or (magnesium adj fluoride)) with anneal\$4)	EPO; JPO; DERWENT; IBM_TDB	2004/01/29 14:11
87	16	((MgF2 or "MgF.sub.2" or (magnesium adj fluoride)) with (heat\$3 adj treat\$4))	EPO; JPO; DERWENT; IBM_TDB	2004/01/29 14:12
88	17	((MgF2 or "MgF.sub.2" or (magnesium adj fluoride)) same (anneal\$4 or (heat\$3 adj treat\$5))) same (dens\$10 or void or hard\$5 or porous or nonporous or poros\$4 or pack\$5)	USPAT; US-PGPUB	2004/01/29 14:17
89	119	((fluoride) with (coat\$3 or film or layer) same (anneal\$4 or (heat\$3 adj treat\$5))) same (dens\$10 or void or hard\$5 or porous or nonporous or poros\$4 or pack\$5)	USPAT; US-PGPUB	2004/01/29 14:17
90	12	((fluoride) with (coat\$3 or film or layer) with (anneal\$4 or (heat\$3 adj treat\$5))) with (dens\$10 or void or hard\$5 or porous or nonporous or poros\$4 or pack\$5)	USPAT; US-PGPUB	2004/01/29 14:26
91	6688	((anneal\$4 or (heat\$3 adj treat\$5))) with (dens\$10 or void or hard\$5 or porous or nonporous or poros\$4 or pack\$5) with temperature	USPAT; US-PGPUB	2004/01/29 14:26
92	0	((anneal\$4 or (heat\$3 adj treat\$5))) with (dens\$10 or void or hard\$5 or porous or nonporous or poros\$4 or pack\$5) with temperature with (result near2 effective)	USPAT; US-PGPUB	2004/01/29 14:27
93	472	((anneal\$4 or (heat\$3 adj treat\$5))) with (dens\$10 or void or hard\$5 or porous or nonporous or poros\$4 or pack\$5) with temperature with (determin\$5 or depend\$5 or optim\$8 or routine or experiment\$6)	USPAT; US-PGPUB	2004/01/29 14:28

94	8	((anneal\$4 or (heat\$3 adj treat\$5))) with (dens\$10 or void or hard\$5 or porous or nonporous or poros\$4 or pack\$5) with temperature with (determin\$5 or depend\$5 or optim\$8 or routine or experiment\$6)) and ((427/585,593,596,255.28,255.39).CCLS.) ((427/372.2,383.1).CCLS.) ((423/490,497).CCLS.) ((118/715,725,728).CCLS.))	USPAT; US-PGPUB	2004/01/29 14:28
95	2926	((anneal\$4 or (heat\$3 adj treat\$5))) with temperature with (determin\$5 or depend\$5 or optim\$8 or routine or experiment\$6) with time	USPAT; US-PGPUB	2004/01/29 14:31
96	46	((anneal\$4 or (heat\$3 adj treat\$5))) with temperature with (determin\$5 or depend\$5 or optim\$8 or routine or experiment\$6) with time) and ((427/585,593,596,255.28,255.39).CCLS.) ((427/372.2,383.1).CCLS.) ((423/490,497).CCLS.) ((118/715,725,728).CCLS.))	USPAT; US-PGPUB	2004/01/29 14:29
97	101	((427/372.2,383.1).CCLS.) and ((anneal\$4 or (heat\$3 adj treat\$5))) with temperature with time)	USPAT; US-PGPUB	2004/01/29 14:33
98	12	((anneal\$4 or (heat\$3 adj treat\$5))) with temperature with (result near2 effective))	USPAT; US-PGPUB	2004/01/29 15:02
99	0	((MgF2 or (magnesium adj fluoride) or "MgF.sub.2") with (coat\$3 or film or layer or deposit\$3 or apply\$3 or \$4PVD or \$4CVD or EB or (electron adj beam))) and (temperature with ("250" or "300")) and ((vacuum or pressure) with ("-6"))	USPAT; US-PGPUB	2004/01/29 15:04
100	174	((MgF2 or (magnesium adj fluoride) or "MgF.sub.2") with (coat\$3 or film or layer or deposit\$3 or apply\$3 or \$4PVD or \$4CVD or EB or (electron adj beam))) and (temperature with ("250" or "300")) and ((vacuum or pressure or torr))	USPAT; US-PGPUB	2004/01/29 15:06
101	51	((MgF2 or (magnesium adj fluoride) or "MgF.sub.2") with (coat\$3 or film or layer or deposit\$3 or apply\$3 or \$4PVD or \$4CVD or EB or (electron adj beam))) and ((temperature with ("250" or "300")) same ((vacuum or pressure or torr)))	USPAT; US-PGPUB	2004/01/29 15:07
102	9	((MgF2 or (magnesium adj fluoride) or "MgF.sub.2") with (coat\$3 or film or layer or deposit\$3 or apply\$3 or \$4PVD or \$4CVD or EB or (electron adj beam))) and (temperature with ("250" or "300")) and ((vacuum or pressure or torr))) and ((427/585,593,596,255.28,255.39).CCLS.) ((427/372.2,383.1).CCLS.) ((423/490,497).CCLS.) ((118/715,725,728).CCLS.))	USPAT; US-PGPUB	2004/01/29 15:06
103	6	((MgF2 or (magnesium adj fluoride) or "MgF.sub.2") with (\$4PVD or \$4CVD or EB or (electron adj beam) or (vapor adj deposit\$4))).ti,ab.	USPAT; US-PGPUB	2004/01/29 15:15
104	131	((MgF2 or (magnesium adj fluoride) or "MgF.sub.2") with (\$4PVD or \$4CVD or EB or (electron adj beam) or (vapor adj deposit\$4)))	EPO; JPO; DERWENT; IBM_TDB	2004/01/29 15:09
105	33	((MgF2 or (magnesium adj fluoride) or "MgF.sub.2") with (\$4PVD or \$4CVD or EB or (electron adj beam) or (vapor adj deposit\$4))) and ((temperature or temp\$10 or celcius or C or F or K or kelvin) and (pressure or vacuum or torr or pascal or atm or atmosphere))	EPO; JPO; DERWENT; IBM_TDB	2004/01/29 15:10

106	8	((MgF2 or (magnesium adj fluoride) or "MgF.sub.2") with (\$4PVD or \$4CVD or EB or (electron adj beam) or (vapor adj deposit\$4))) and (temperature near5 ("300" or "250")) and (pressure or vacuum)	USPAT; US-PGPUB	2004/01/29 15:15
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